

MICRO

ELECTRONICS

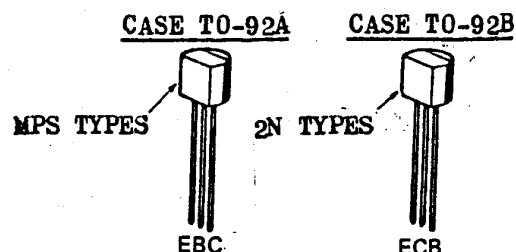
MPS/2N2923,4,5
and similar types

NPN
SILICON
TRANSISTOR

DESCRIPTION

The above types are NPN silicon planar epitaxial transistors for use in AF small amplifiers and direct coupled circuits.

Their maximum power dissipation =
160mW at $T_a = 25^\circ\text{C}$.



DEVICE SPECIFICATIONS ($T_a = 25^\circ\text{C}$)

DEVICE TYPE	LVCEO (V)	BVEBO (V)	ICBO @ VCB (nA) (V)	HFE @ IC/VCE (mA)(V)	VCE(sat) @ IC/IB (V) (mA)(mA)	NOTE
	min	min	max	min-max	max	
MPS/2N2711	18	5	500 @ 18	30-90 @ 2/4.5		$C_{ob} < 4\text{pF}$ @ $V_{CB}=10\text{V}$
MPS/2N2712	18	5	500 @ 18	75-225 @ 2/4.5		$C_{ob} < 12\text{pF}$ @ $V_{CB}=10\text{V}$
MPS/2N2716	18	5	500 @ 18	75-225 @ 2/4.5		$C_{ob} < 5\text{pF}$ @ $V_{CB}=10\text{V}$
MPS/2N2923	25	5	500 @ 25	90-180* @ 2/10		* h_{fe} @ 1KHz
MPS/2N2924				150-300* @ 2/10		
MPS/2N2925				235-470* @ 2/10		
MPS/2N3390	25	5	100 @ 18	400-800 @ 2/4.5		
MPS/2N3391				250-500 @ 2/4.5		
MPS/2N3392				150-300 @ 2/4.5		
MPS/2N3393				90-180 @ 2/4.5		
MPS/2N3394				55-110 @ 2/4.5		
MPS/2N3395				150-500 @ 2/4.5		
MPS/2N3396				90-500 @ 2/4.5		
MPS/2N3397				55-500 @ 2/4.5		
MPS/2N3398				55-800 @ 2/4.5		
MPS 6565	45	4	100 @ 30	40-160 @ 10/10	0.4 @ 10/1	$C_{ob} < 3.5\text{pF}$ @ $V_{CB}=10\text{V}$ $f_T > 200\text{MHz}$ @ $I_C=10\text{mA}$ $V_{CE}=10\text{V}$
MPS 6566				100-400 @ 10/10		
MPS 6573	35	4	100 @ 35	100- @ 0.1/5 200-500 @ 10/5	0.5 @ 10/1	* HFE GROUPINGS : Y = 100-150 B = 125-185 G = 150-225 S = 200-300
MPS 6574	35	4	100 @ 35	100-300* @ 1/5	0.5 @ 10/1	
MPS 6575	45	4	100 @ 45	100- @ 0.1/5 200-500 @ 10/5	0.5 @ 10/1	
MPS 6576	45	4	100 @ 45	100-300* @ 1/5	0.5 @ 10/1	



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